

Dual N-Channel 40 V (D-S) Power MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (mΩ) (Typ.)	I _D (A) ^a	Q _g (Typ.)
40	4.2 at V _{GS} = 10 V	75	35 nC
	5.3 at V _{GS} = 4.5 V		

FEATURES

- DT-Trench Power MOSFET
- Very low on-resistance
- 100 % Rg and UIS Tested



RoHS
COMPLIANT

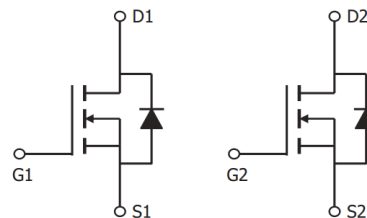
APPLICATIONS

- Power Management
- Motor Drivers
- DC-DC Converters

DFN5X6 Pin Configuration



Top View



N1-Channel MOSFET

N2-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	75
		T _C = 100 °C	56
Pulsed Drain Current	I _{DM}	300	A
Single Avalanche Energy ^a	E _{AS}	450	mJ
Maximum Power Dissipation ^a	P _D	T _C = 25 °C	70 ^b
		T _C = 100 °C	44.8 ^b
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	1.8	

Notes

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

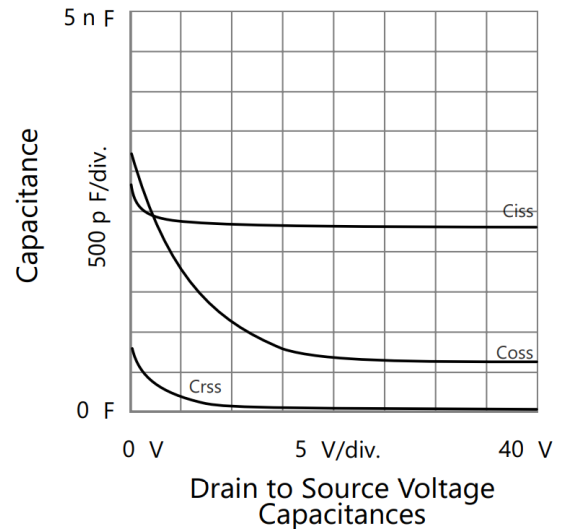
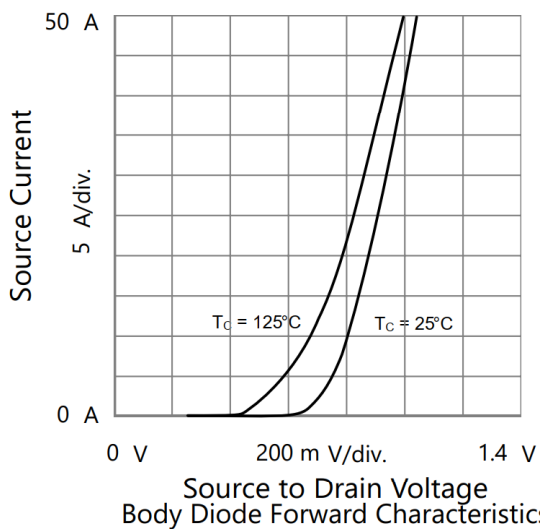
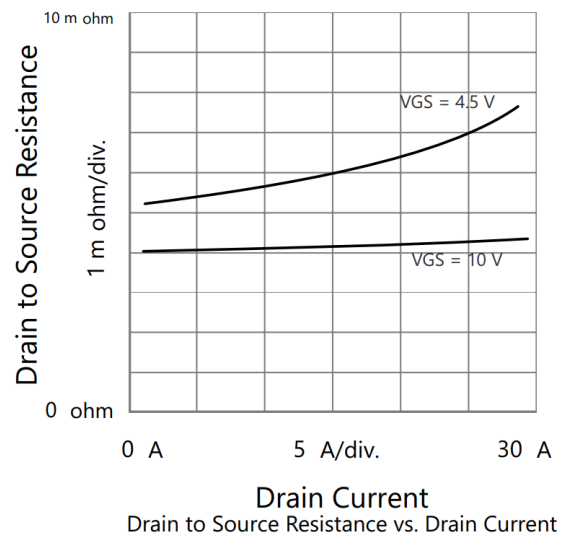
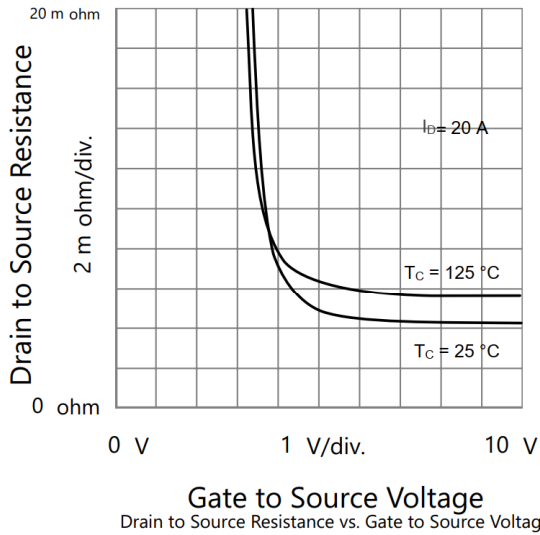
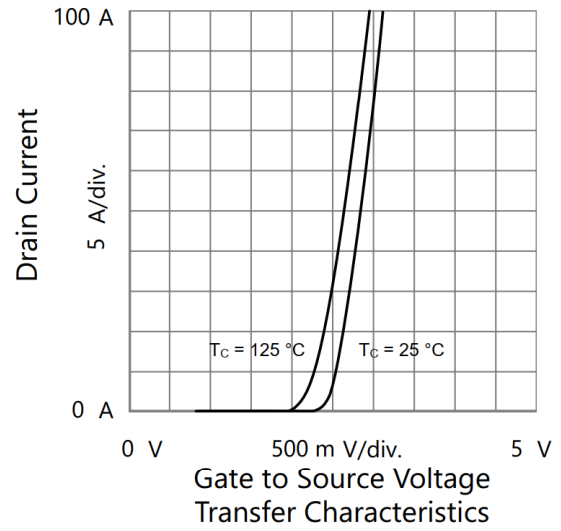
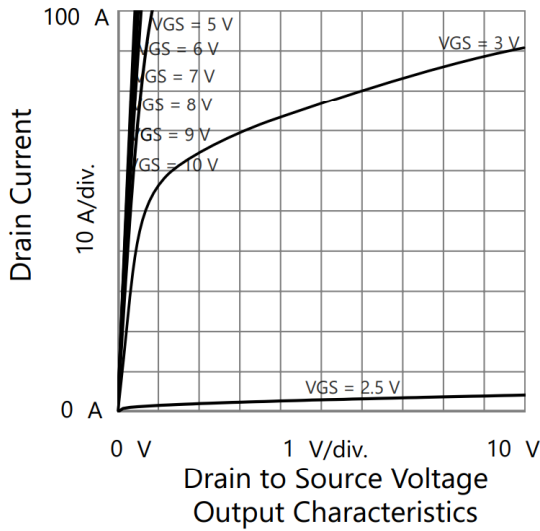
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	-	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	75	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	-	4.2	5	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$	-	5.3	6.5	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 5\text{ V}, I_D = 20\text{ A}$	-	60	-	S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}, f = 1\text{ MHz}$	-	2195	-	pF
Output Capacitance	C_{oss}		-	703	-	
Reverse Transfer Capacitance	C_{rss}		-	34	-	
Total Gate Charge ^c	Q_g	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	-	35	-	nC
Gate-Source Charge ^c	Q_{gs}		-	6.3	-	
Gate-Drain Charge ^c	Q_{gd}		-	5	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$	-	2	-	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_g = 2\text{ }\Omega$ $I_D = 20\text{ A}, V_{GEN} = 10\text{ V},$	-	12	-	ns
Rise Time ^c	t_r		-	10	-	
Turn-Off Delay Time ^c	$t_{d(off)}$		-	42	-	
Fall Time ^c	t_f		-	8	-	
Drain-Source Body Diode Ratings and Characteristics ^b ($T_C = 25\text{ }^\circ\text{C}$)						
Continuous Source Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	75	A
Pulsed Source Current	I_{SM}		-	-	300	A
Forward Voltage ^a	V_{SD}	$I_F = 20\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	14	-	ns
Reverse Recovery Charge	Q_{rr}		-	20	-	nC

Notes

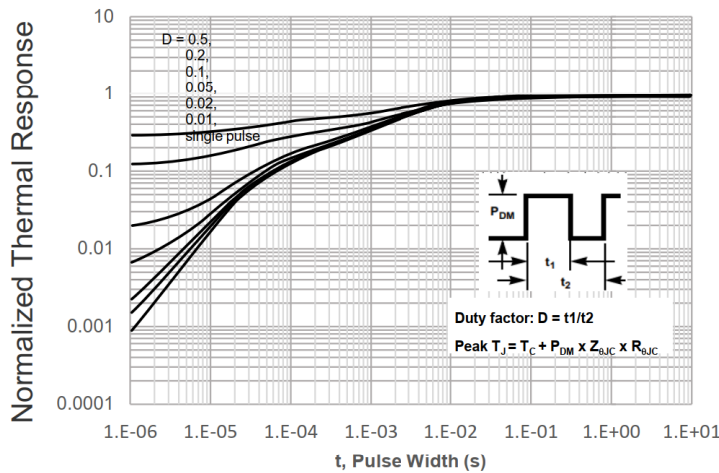
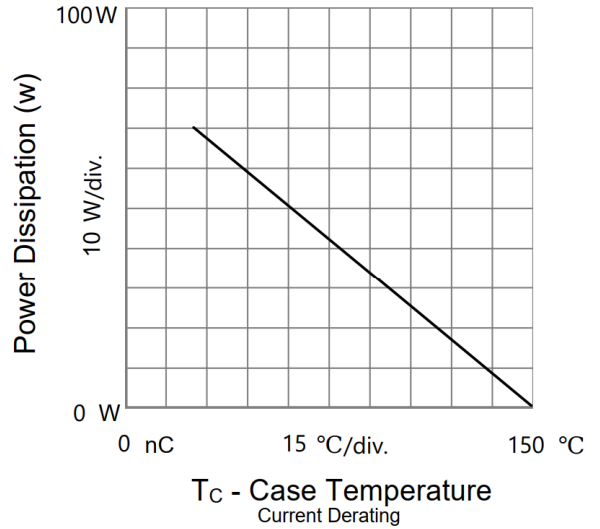
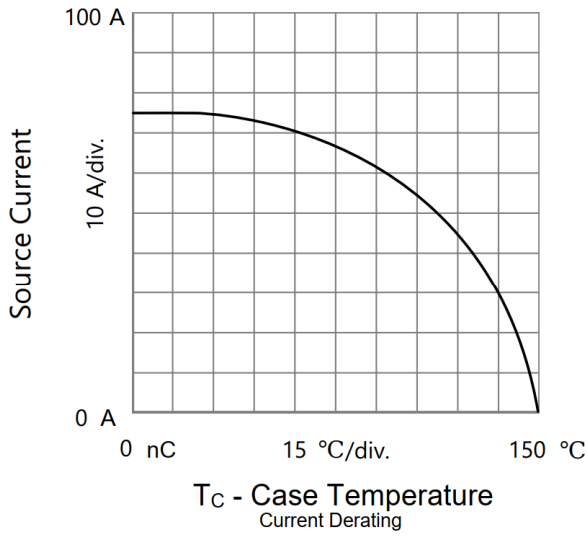
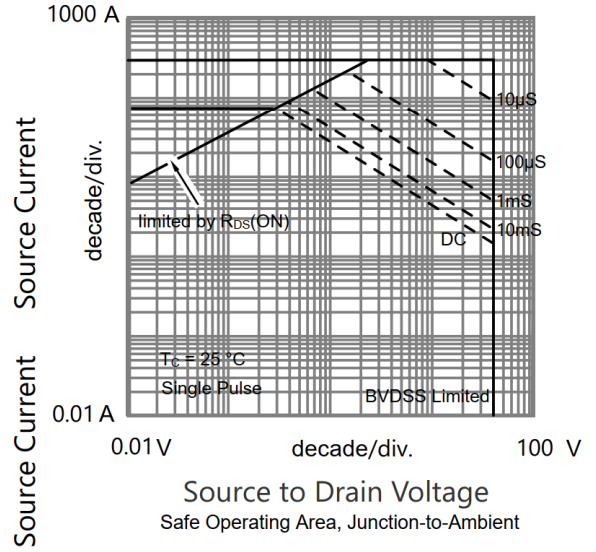
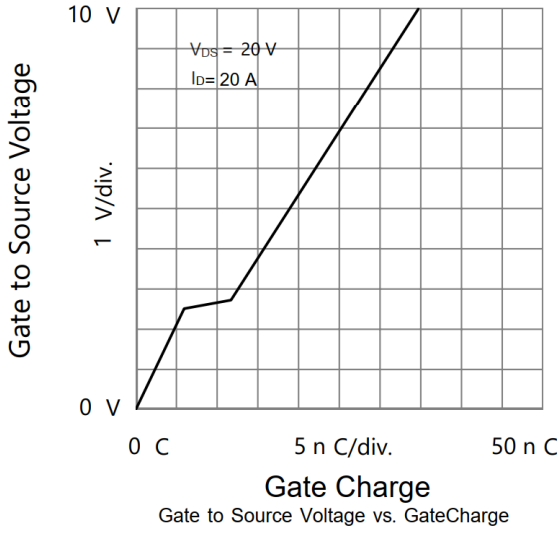
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

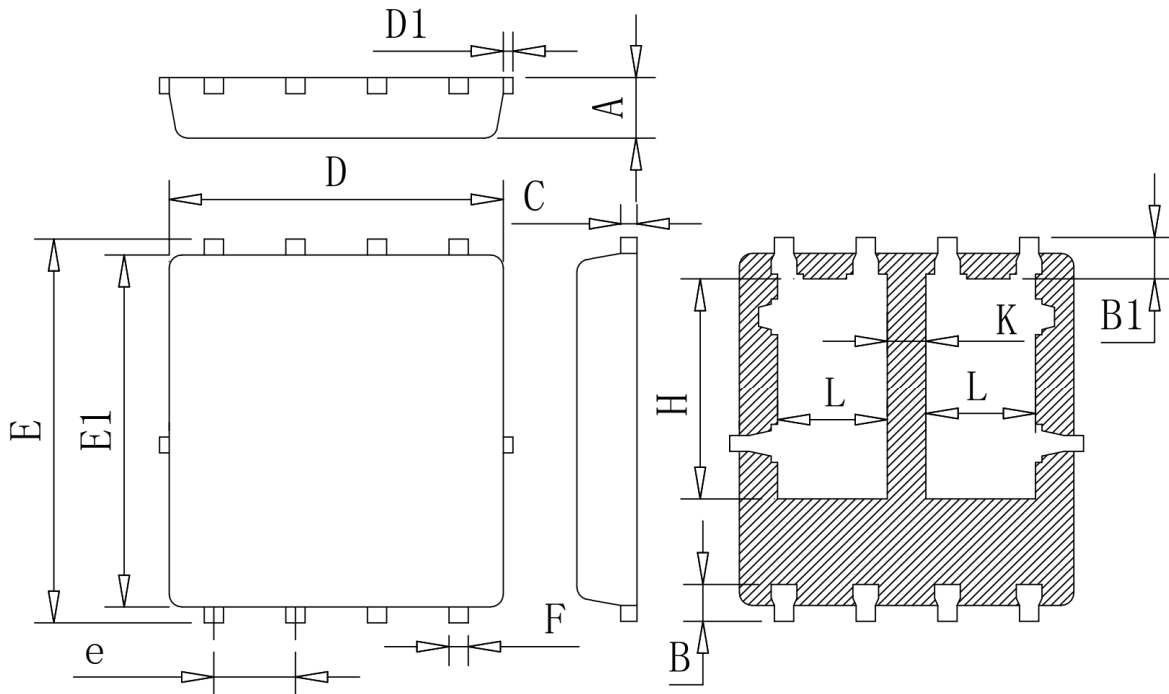


TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance

DFN5X6-8L-D PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Typ	Max
A	0.85	0.95	1.05
B	0.46	0.58	0.73
B1	0.52	0.65	0.78
C	0.18	0.254	0.32
D	4.70	5.20	5.50
D1	-	-	0.18
E	5.75	6.05	6.35
E1	5.35	5.65	5.85
e	1.15	1.27	1.50
F	0.15	0.30	0.50
H	3.15	3.47	3.80
L	1.35	1.70	2.10
K	0.35	0.60	1.00

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